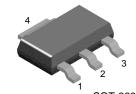


FZT790A

PNP Low Saturation Transistor

• These devices are designed with high current gain and low saturation voltage with collector currents up to 3A continuous.



1. Base 2.4. Collector 3. Emitter

Absolute Maximum Ratings * T_C=25°C unless otherwise noted

Symbol	Parameter	Value	Units
V _{CEO}	Collector-Emitter Voltage	-40	V
V _{CBO}	Collector-Base Voltage	-50	V
V _{EBO}	Emitter-Base Voltage	-5	V
I _C	Collector Current - Continuous	-3	Α
T _J , T _{STG}	Operating and Storage Junction Temperature Range	- 55 ~ +150	°C

^{*} These ratings are limiting values above which the serviceability of any semiconductor device may be impaired.

Electrical Characteristics T_A=25°C unless otherwise noted

Symbol	Parameter	Test Conditions	Min.	Max.	Units
Off Characte		Test Conditions	IVIIII.	IVIAA.	Office
			1		П
BV _{CEO}	Collector-Emitter Breakdown Voltage	$I_C = -10 \text{mA}, I_B = 0$	-40		V
BV _{CBO}	Collector-Emitter Breakdown Voltage	$I_C = -100\mu A, I_E = 0$	-50		V
BV _{EBO}	Emitter-Base Breakdown Voltage	$I_E = -100 \mu A, I_C = 0$	-5.0		V
I _{CBO}	Collector Cut-off Current	$V_{CB} = -30V, I_{E} = 0$ $V_{CB} = -30V, I_{E} = -1.0A, I$			
				-0.25	mV
		$_{B} = -10 \text{mA}$ $I_{C} = -2.0 \text{A}, I_{B} = -50 \text{mA}$		-0.45 -0.75	
V _{BE(sat)}	Base-Emitter Saturation Voltage	$I_C = -1.0A, I_B = -10mA$		-1.0	V
V _{BE(on)}	Base-Emitter On Voltage	$I_C = -1.0A, V_{CE} = -2.0V$		-1.0	V
	Characteristics	<u>, , , , , , , , , , , , , , , , , , , </u>			
f _T	Transition Frequency	$I_{C} = -50 \text{mA}, V_{CE} = -5.0 \text{V},$ f = 50 MHz	100		MHz

* Pulse Test: Pulse Width ≤300μs, Duty Cycle ≤ 2.0%

Thermal Characteristics

Symbol	Parameter	Max.	Units	
P _D	Total Device Dissipation	2	W	
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient		°C/W	

These ratings are based on a maximum junction temperature of 150degrees C.
These are steady state limits. The factory should be consulted on applications involving pulsed or low duty cycle operations.

Typical Characteristics

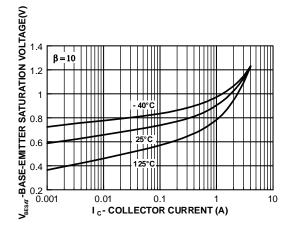


Figure 1. Base-Emitter Saturation Voltage vs Collector Current

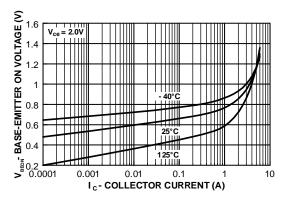


Figure 2. Base-Emitter On Voltage vs Collector Current

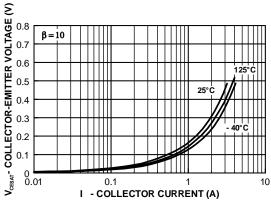


Figure 3. Collector-Emitter Saturation Voltage vs Collector Current

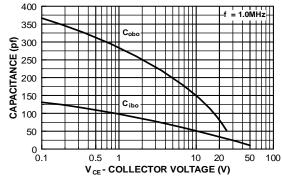


Figure 4. Input/Output Capacitance vs Reverse Bias Voltage

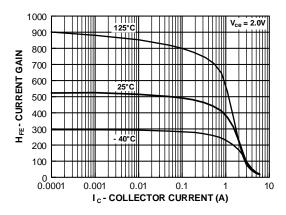


Figure 5. Current Gain vs Collector Current

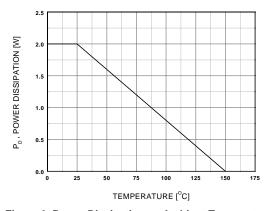
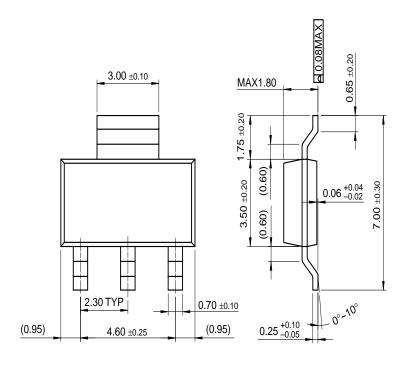
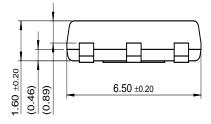


Figure 6. Power Dissipation vs Ambient Temperature

Package Dimensions

SOT-223





Dimensions in Millimeters

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E ² CMOS™	HiSeC™	MSXPro™	Quiet Series™	TruTranslation™
EnSigna™	I^2C^{TM}	OCX^{TM}	RapidConfigure™	UHC™
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The Power Franchise™		OPTOLOGIC [®]	SILENT SWITCHER®	VCX^{TM}
Programmable Ad	ctive Droop™	OPTOPLANAR™	SMART START™	

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